

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device including a transistor formed by means of a common contact hole that
5 connects a gate electrode, and a diffused layer forming a source/drain terminal; and a semiconductor device comprising the gate electrode of the transistor, and a connecting terminal to which capacitance between substrates and capacitance between the gate electrode and the source/drain terminal are added,
10 thereby improving the soft error resistance caused by alpha rays and neutron beams.

1. A semiconductor device comprising:
a transistor formed by means of a common contact hole that connects a gate electrode, and a diffused layer forming a source/drain terminal;
and
a semiconductor device comprising the gate electrode of the transistor, and a connecting terminal to which capacitance between substrates and capacitance between the gate electrode and the source/drain terminal are added,
thereby improving the soft error resistance caused by alpha rays and neutron beams.